

Gallium Arsenide Schottky Rectifier

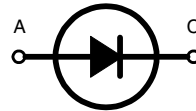
$$I_{FAV} = 23 \text{ A}$$

$$V_{RRM} = 180 \text{ V}$$

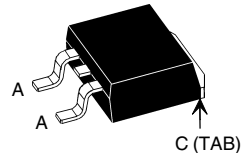
$$C_{Junction} = 33 \text{ pF}$$

Preliminary Data

| V_{RSM} V | V_{RRM} V | Type |
|----------------|----------------|--------------|
| 180 | 180 | DGS 20-018AS |



TO-263 AB



A = Anode, C = Cathode, TAB = Cathode

| Symbol | Conditions | Maximum Ratings | |
|-----------|---|-----------------|------------------|
| I_{FAV} | $T_C = 25^\circ\text{C}$; DC | 23 | A |
| I_{FAV} | $T_C = 90^\circ\text{C}$; DC | 17 | A |
| I_{FSM} | $T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine | 30 | A |
| T_{VJ} | | -55...+175 | $^\circ\text{C}$ |
| T_{stg} | | -55...+150 | $^\circ\text{C}$ |
| P_{tot} | $T_C = 25^\circ\text{C}$ | 48 | W |

Features

- Low forward voltage
- Very high switching speed
- Low junction capacity of GaAs
 - low reverse current peak at turn off
- Soft turn off
- Temperature independent switching behaviour
- High temperature operation capability
- Epoxy meets UL 94V-0

Applications

- MHz Switched mode power supplies (SMPs)
- Small size SMPs
- High frequency converters
- Resonant converters

| Symbol | Conditions | Characteristic Values | |
|------------|--|-----------------------|--------|
| | | typ. | max. |
| I_R ① | $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ | | 2.0 mA |
| | $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$ | 2.0 | mA |
| V_F | $I_F = 7.5 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ | 0.8 | V |
| | $I_F = 7.5 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ | 0.8 | 1.0 V |
| C_J | $V_R = 100 \text{ V}$; $T_{VJ} = 125^\circ\text{C}$ | 33 | pF |
| R_{thJC} | | 3.1 | K/W |
| Weight | | 2 | g |

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

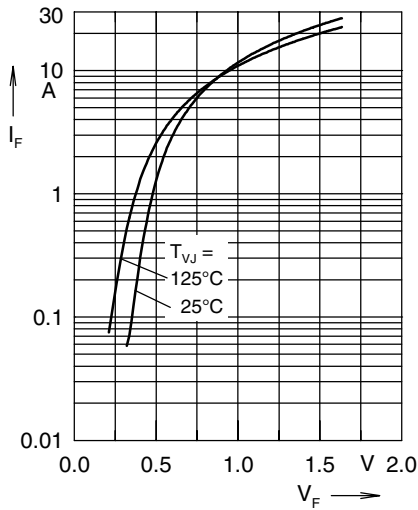


Fig. 1 typ. forward characteristics

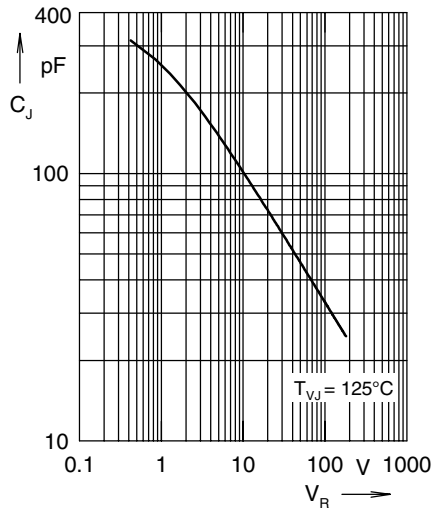


Fig. 2 typ. junction capacity versus blocking voltage

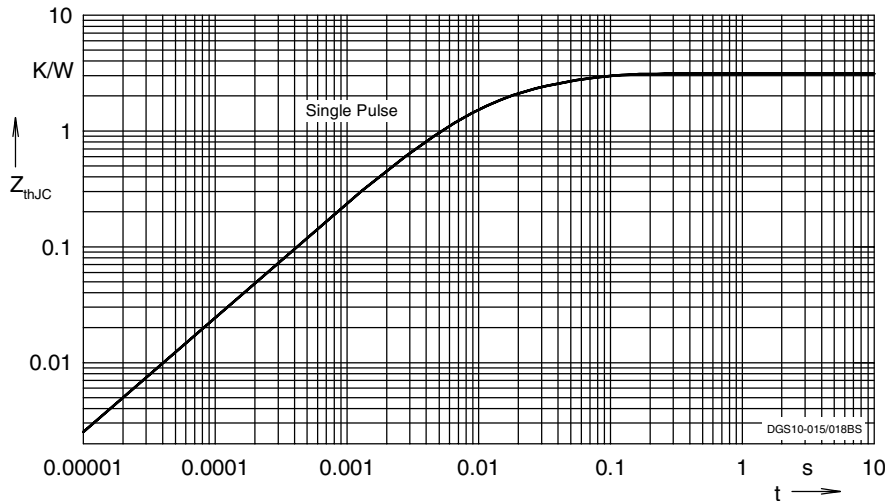
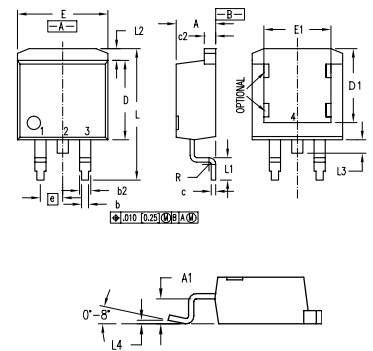


Fig. 3 typ. thermal impedance junction to case

Note:
explanatory comparison of the basic operational behaviour of rectifier diodes and Gallium Arsenide Schottky diodes:

| | Rectifier Diode | GaAs Schottky Diode |
|--------------------------|--|---|
| conduction | by majority + minority carriers | by majority carriers only |
| forward characteristics | $V_F (I_F)$ | $V_F (I_F)$, see Fig. 1 |
| turn off characteristics | extraction of excess carriers causes temperature dependant reverse recovery (t_{rr} , I_{RM} , Q_{rr}) | reverse current charges junction capacity C_J , see Fig. 2; |
| turn on characteristics | delayed saturation leads to V_{FR} | not temperature dependant no turn on overvoltage peak |

Outline TO-263 AB



| Dim. | Millimeter | | Inches | |
|------|------------|-------|----------|------|
| | Min. | Max. | Min. | Max. |
| A | 4.06 | 4.83 | .160 | .190 |
| A1 | 2.03 | 2.79 | .080 | .110 |
| b | 0.51 | 0.99 | .020 | .039 |
| b2 | 1.14 | 1.40 | .045 | .055 |
| c | 0.46 | 0.74 | .018 | .029 |
| c2 | 1.14 | 1.40 | .045 | .055 |
| D | 8.64 | 9.65 | .340 | .380 |
| D1 | 8.00 | 8.89 | .315 | .350 |
| E | 9.65 | 10.29 | .380 | .405 |
| E1 | 6.22 | 8.13 | .245 | .320 |
| e | 2.54 BSC | | .100 BSC | |
| L | 14.61 | 15.88 | .575 | .625 |
| L1 | 2.29 | 2.79 | .090 | .110 |
| L2 | 1.02 | 1.40 | .040 | .055 |
| L3 | 1.27 | 1.78 | .050 | .070 |
| L4 | 0 | 0.20 | 0 | .008 |
| R | 0.46 | 0.74 | .018 | .029 |